

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

- 1-8. (Cancelled)
9. (Currently Amended) A semiconductor device comprising:
a substrate having a region irradiated with radiating rays,
crystal defects within the region irradiated,
impurity regions formed in the substrate, and
a metal wiring layer located over the substrate, the metal wiring layer being connected to each of the impurity regions, the metal wiring layer being made of a light metal, the metal wiring layer having an opening above the region irradiated, so that radiating rays passing to the region irradiated through the opening generate the crystal defects ~~only~~ under the opening and so that a smaller amount of radiating rays are irradiated to regions in said substrate except said region under the opening.
10. (Currently Amended) The semiconductor device in accordance with Claim 9, wherein the metal wiring layer is formed in a thickness so ~~as to restrict penetration of the radiating rays into the region irradiated~~ the smaller amount of radiating rays are irradiated to the regions except the region under the opening.
11. (Previously Presented) The semiconductor device in accordance with Claim 10, wherein an insulating layer is formed above the region irradiated, the opening being on the insulating layer.
12. (Previously Presented) The semiconductor device in accordance with Claim 11, wherein the metal wiring layer covers a part of the insulating layer.
13. (Currently Amended) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is an insulated gate bipolar transistor, wherein the impurity region is a source region, and wherein the region irradiated is a ~~positive-negative junction~~ positive-negative junction where a parasitic diode is generated.

14. (Previously Presented) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is a metal oxide semiconductor field effect transistor, wherein the impurity region is a source region, and wherein the region irradiated is a positive-negative junction region where a parasitic diode is generated.
